

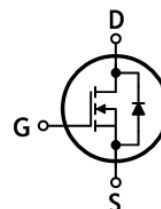
SWITCHING REGULATOR APPLICATION

Features

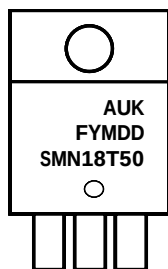
- Drain-Source breakdown voltage: $BV_{DSS} = 500V$
- Low gate charge: $Q_g = 65nC$ (Typ.)
- Low drain-source On resistance: $R_{DS(on)} = 0.21\Omega$ (Typ.)
- 100% avalanche tested
- RoHS compliant device

Ordering Information

Part Number	Marking	Package
SMN18T50FD	SMN18T50	TO-220F-3L


TO-220F-3L

Marking Information



Column 1: Manufacturer
Column 2: Production Information
 e.g.) FYMDD
 -. F: Factory Management Code
 -. YMDD: Date Code (Year, Month, Date)
Column 3: Device Code

Absolute maximum ratings ($T_c = 25^\circ C$ unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Drain-source voltage	V _{DSS}		500	V
Gate-source voltage	V _{GSS}		±30	V
Drain current (DC) *	I _D	T _c =25°C	18	A
		T _c =100°C	11.4	A
Drain current (Pulsed) *	I _{DM}		72	A
Single pulsed avalanche energy ^(Note 2)	E _{AS}		900	mJ
Repetitive avalanche current ^(Note 1)	I _{AR}		18	A
Repetitive avalanche energy ^(Note 1)	E _{AR}		4.8	mJ
Power dissipation	P _D		48	W
Peak diode recovery dv/dt ^(Note 3)	dv/dt		4.5	V/ns
Junction temperature	T _J		150	°C
Storage temperature range	T _{stg}		-55~150	°C

* Drain current limited by maximum junction temperature

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 2.6	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0$	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$, $V_{DS}=V_{GS}$	2	-	4	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=400\text{V}$, $T_c=125^\circ\text{C}$	-	-	100	μA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=9\text{A}$	-	0.21	0.26	Ω
Forward transfer conductance (Note 4)	g_{fs}	$V_{DS}=10\text{V}$, $I_D=9\text{A}$	-	24.6	-	S
Input capacitance	C_{iss}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	3120	-	pF
Output capacitance	C_{oss}		-	355	-	
Reverse transfer capacitance	C_{rss}		-	27	-	
Turn-on delay time (Note 4,5)	$t_{d(on)}$	$V_{DD}=250\text{V}$, $I_D=18\text{A}$, $R_G=25\Omega$	-	95	-	ns
Rise time (Note 4,5)	t_r		-	375	-	
Turn-off delay time (Note 4,5)	$t_{d(off)}$		-	100	-	
Fall time (Note 4,5)	t_f		-	105	-	
Total gate charge (Note 4,5)	Q_g	$V_{DS}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=18\text{A}$	-	65	85	nC
Gate-source charge (Note 4,5)	Q_{gs}		-	17.6	-	
Gate-drain charge (Note 4,5)	Q_{gd}		-	18.4	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	18	A
Source current (Pulsed)	I_{SM}		-	-	72	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=18\text{A}$	-	-	1.4	V
Reverse recovery time (Note 4,5)	t_{rr}	$I_S=18\text{A}$, $V_{GS}=0\text{V}$ $di_S/dt=100\text{A}/\mu\text{s}$	-	507	-	ns
Reverse recovery charge (Note 4,5)	Q_{rr}		-	7.2	-	μC

Note:

1. Repeated rating: Pulse width limited by safe operating area
2. $L=5\text{mH}$, $I_{AS}=18\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
3. $I_S \leq 18\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
4. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature typical characteristics

Electrical Characteristics Curve

Fig. 1 $I_D - V_{DS}$

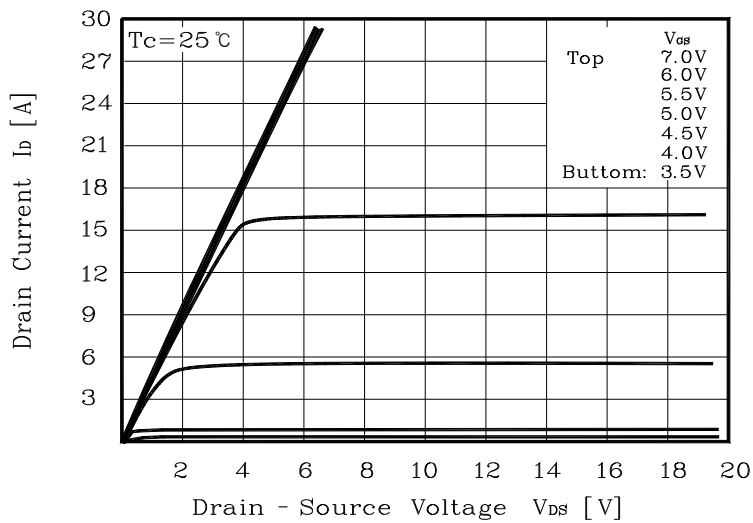


Fig. 2 $I_D - V_{GS}$

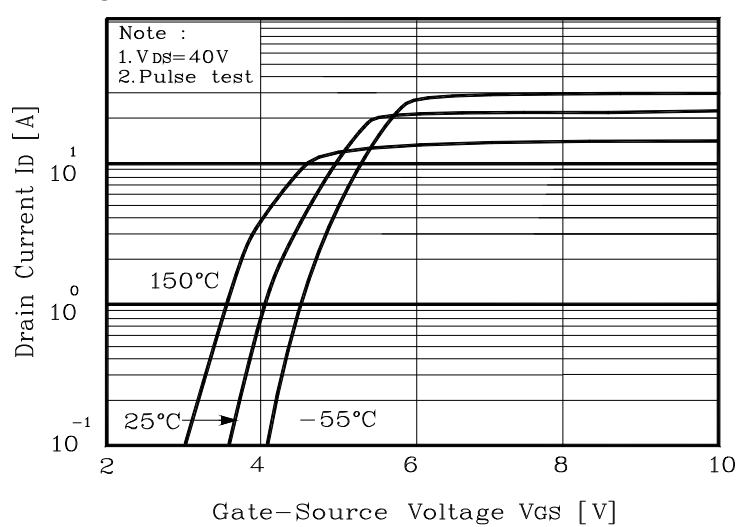


Fig. 3 $R_{DS(ON)} - I_D$

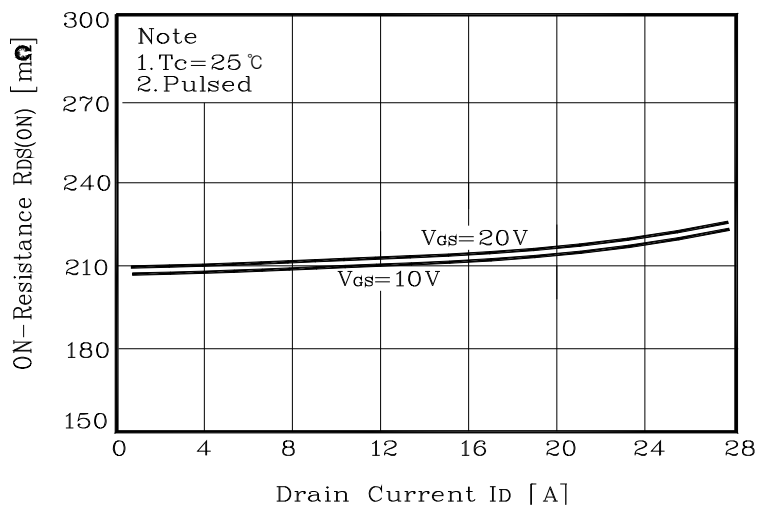


Fig. 4 $I_{DR} - V_{SD}$

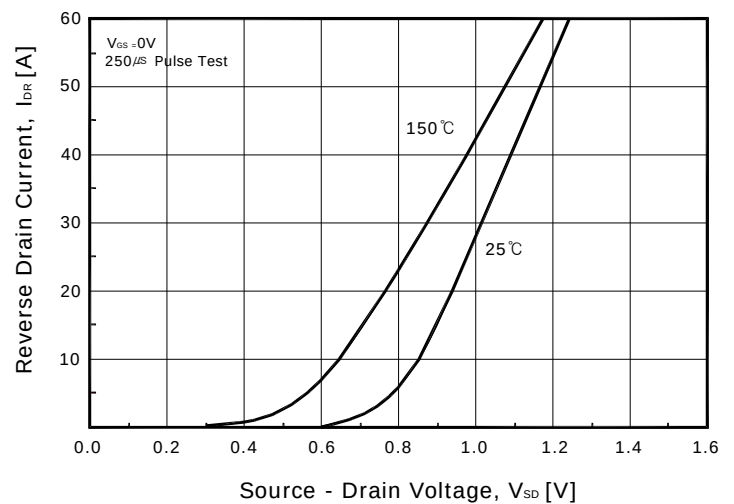


Fig. 5 Capacitance - V_{DS}

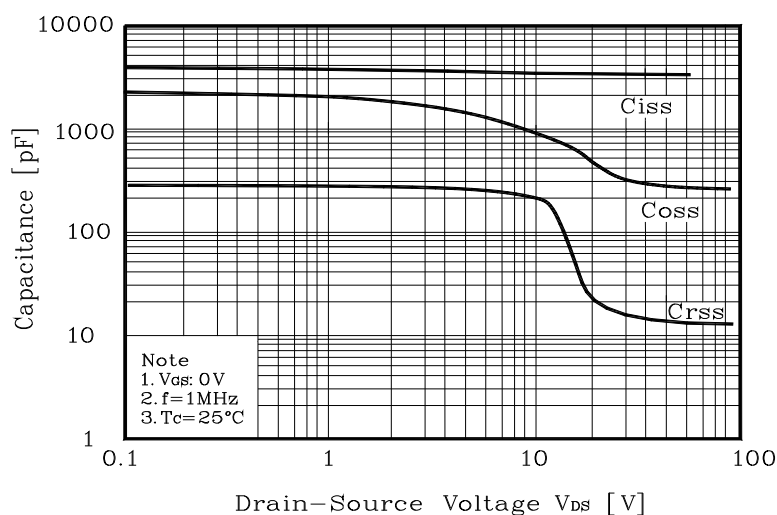
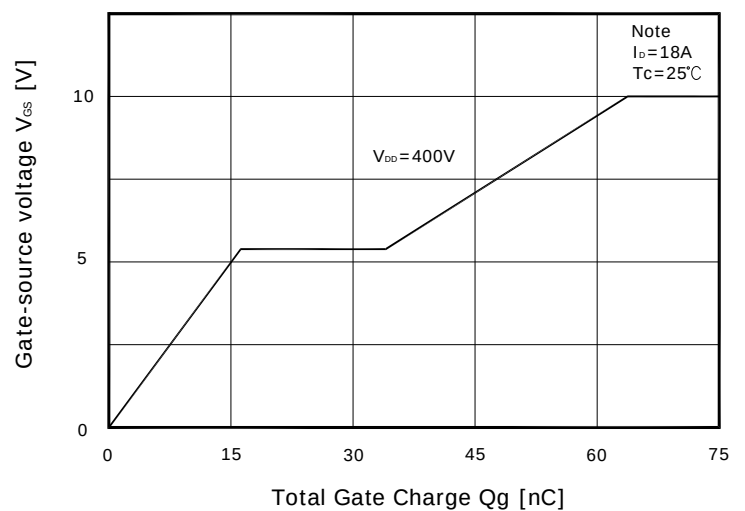


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristics Curve (Continue)

Fig. 7 $BV_{DSS} - T_J$

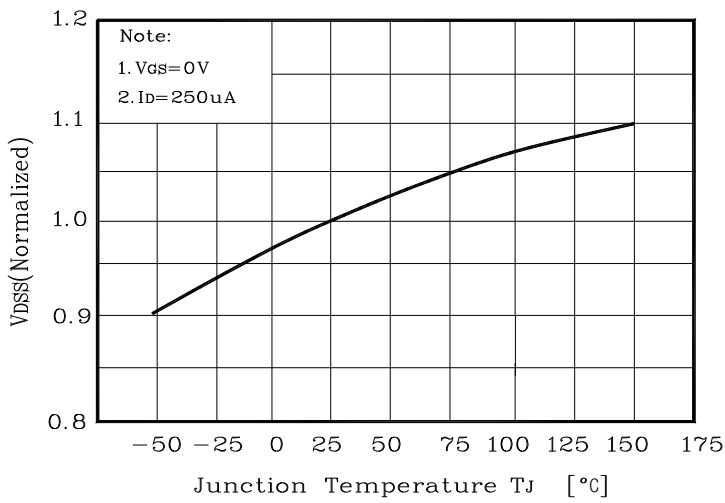


Fig. 8 $R_{DS(ON)} - T_J$

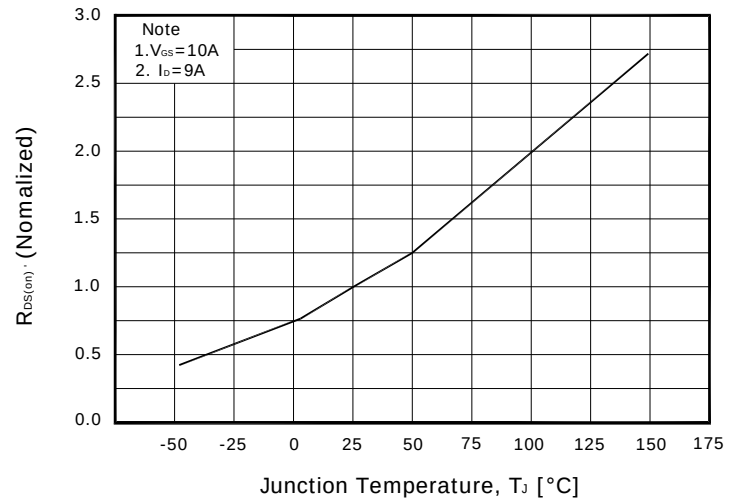


Fig. 9 $I_D - T_C$

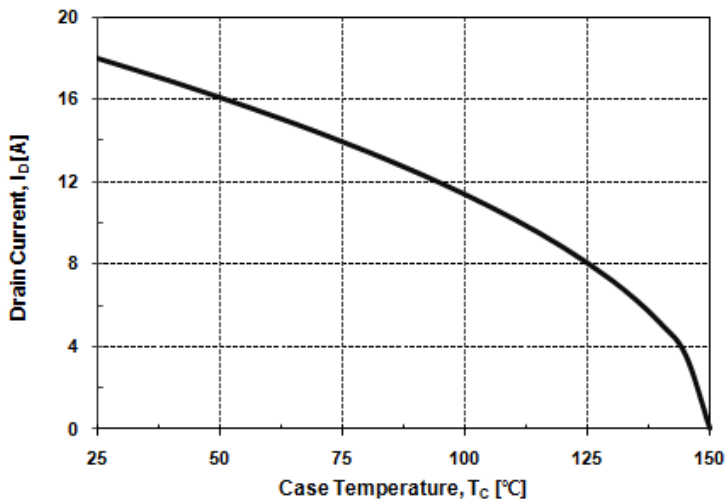


Fig. 10 Safe Operating Area

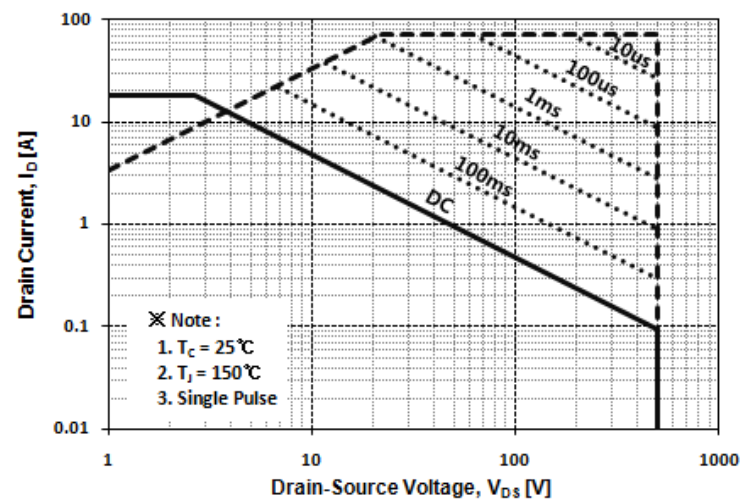


Fig. 11 Transient Thermal Impedance

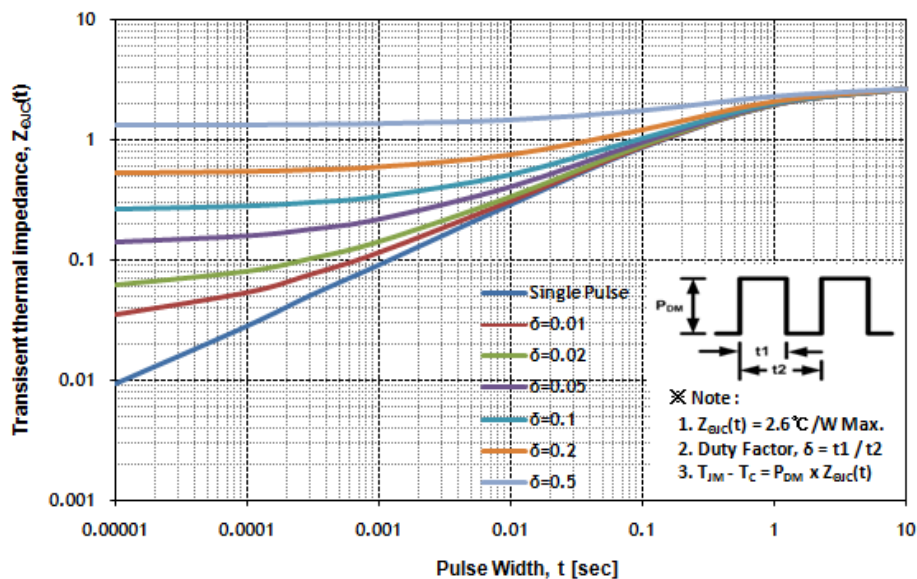


Fig. 12 Gate Charge Test Circuit & Waveform

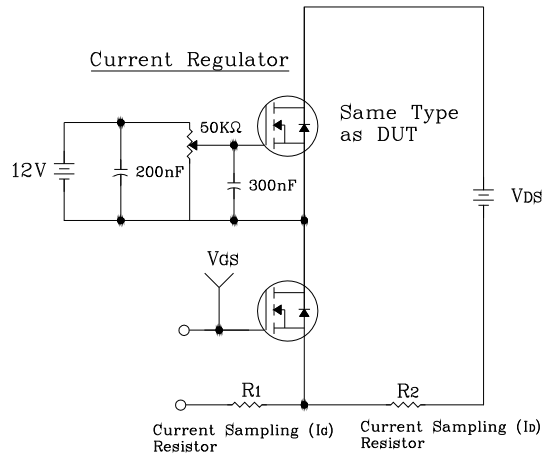
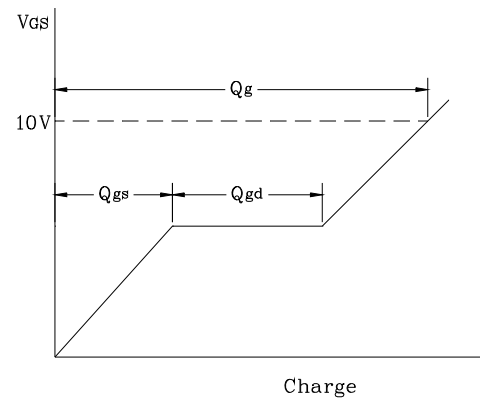


Fig. 13 Resistive Switching Test Circuit & Waveform

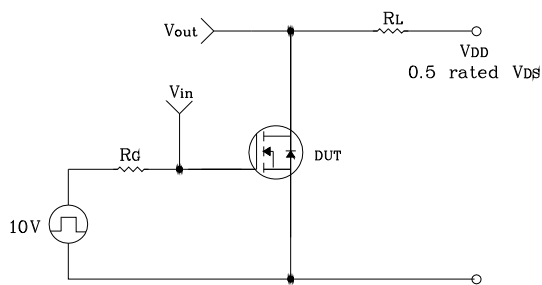
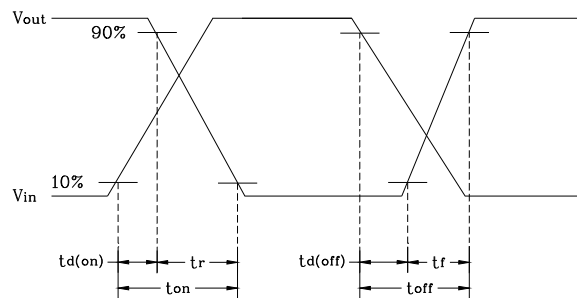


Fig. 14 E_{AS} Test Circuit & Waveform

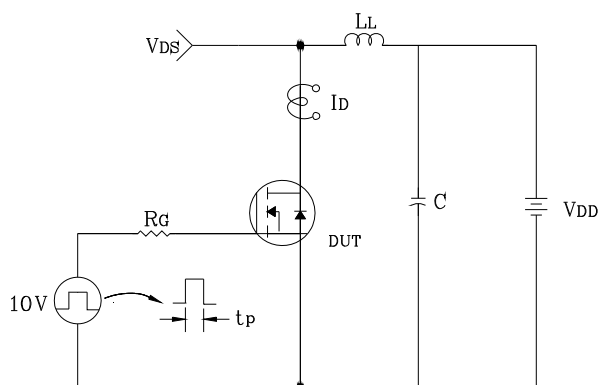
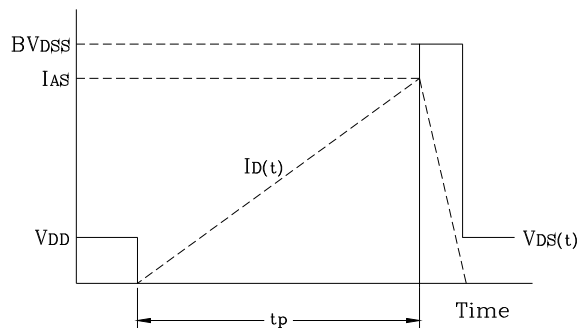
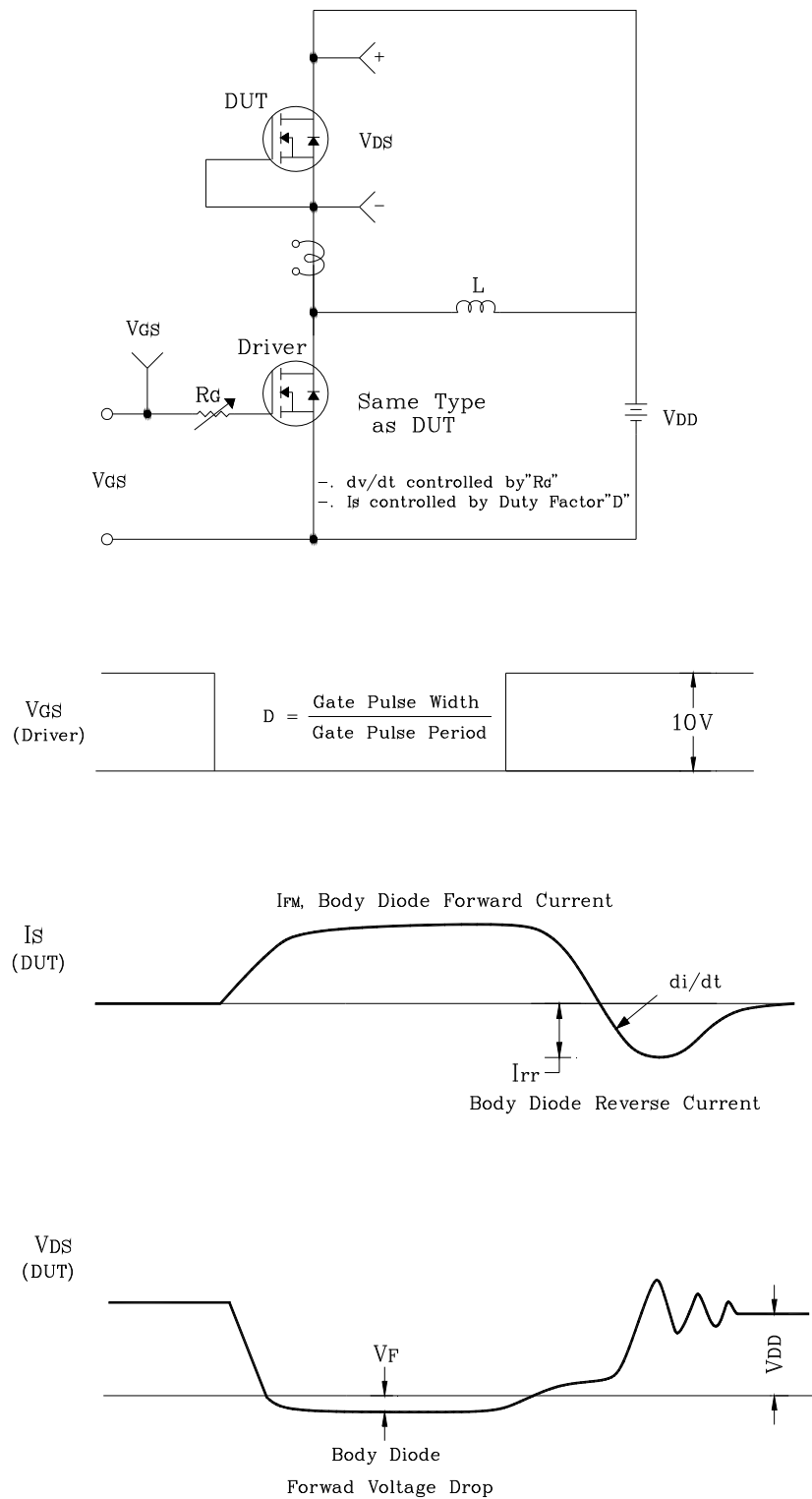
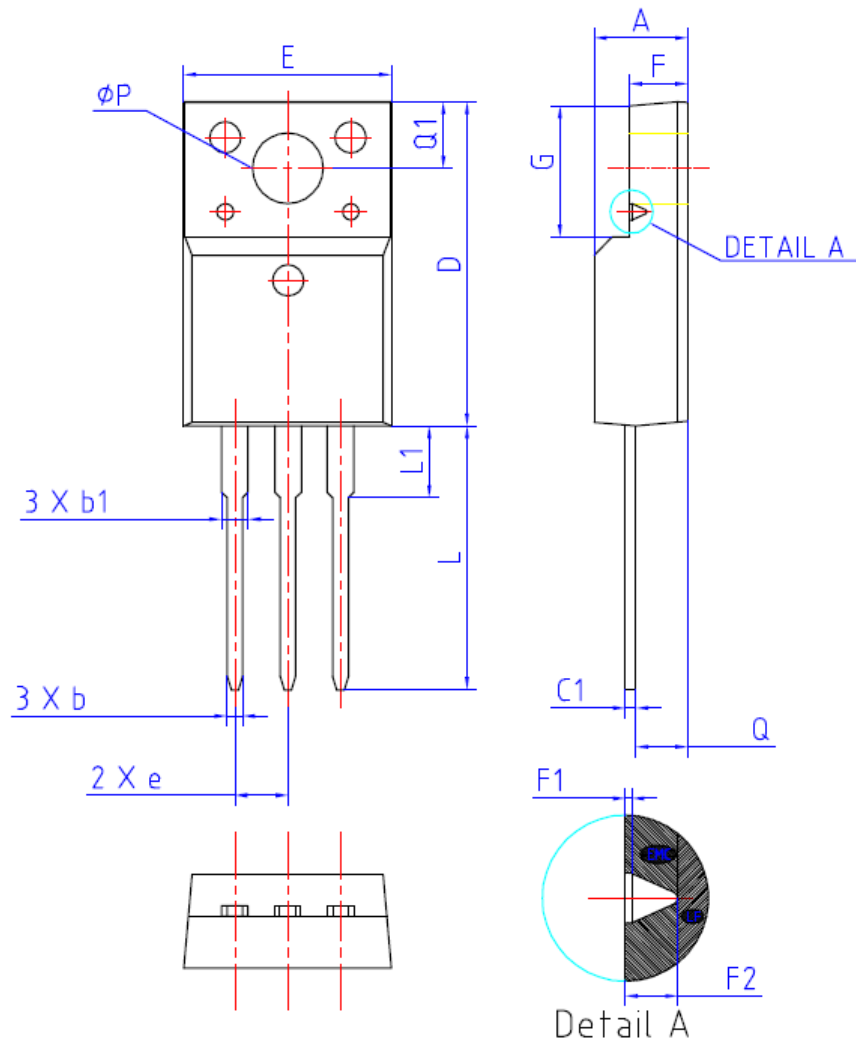


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	4.50	4.70	4.90	
b	0.70	0.80	0.90	
b1	1.33	1.40	1.47	
C1	0.45	0.50	0.60	
D	15.67	15.87	16.07	
E	9.96	10.16	10.36	
e	2.54BSC			
F	2.34	2.54	2.74	
F1	(0.10 REF)			
F2	(0.84 REF)			
G	6.48	6.68	6.88	
L	12.78	12.98	13.18	
L1	3.03	3.23	3.43	
Q	2.56	2.76	2.96	
Q1	3.10	3.30	3.50	
ØP	3.08	3.18	3.28	

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